NSN 5962-01-303-7725

Memory Microcircuit - Page 1 of 1

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View Online at https://aerobasegroup.com/nsn/5962-01-303-7725

Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Monolithic and programmable
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line Dual-in-line
Output Logic Form:
Transistor-transistor logic
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
180.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds propagation delay time, high to low level output and 30.00 nanoseconds propagation delay time, low to high level
output
Memory Device Type:
Pal
Terminal Type And Quantity:
20 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig: